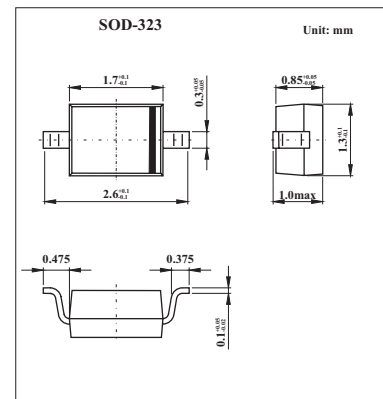


## Silicon Schottky Diode

## BAT14-03W

## ■ Features

- DBS mixer application to 12GHz
- Medium barrier type
- Low capacitance

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	4	V
Forward current	$I_F$	90	mA
Operating temperature range	$T_{op}$	-55 to +125	°C
Storage temperature	$T_{stg}$	-55 to +150	
Total power dissipation	$P_{tot}$	100	mW
Junction ambient <sup>(1)</sup>	$R_{thJA}$	$\leq 450$	°C
Junction-soldering point	$R_{thJS}$	$\leq 690$	K/W

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm<sup>2</sup> Cu.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Min	Typ	Max	Unit	
Breakdown Voltage	$I_{(BR)} = 5 \mu\text{A}$	$V_{(BR)}$	4		V	
Forward voltage	$I_F = 1 \text{ mA}$	$V_F$	0.36	0.43	0.52	V
	$I_F = 10 \text{ mA}$		0.48	0.55	0.66	
Diode capacitance	$V_R = 0; f = 1 \text{ MHz}$	$C_T$		0.22	0.35	pF
Differential forward resistance	$I_F = 10 \text{ mA}/50 \text{ mA}$	$R_F$		5.5		$\Omega$

## ■ Marking

Marking	O
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